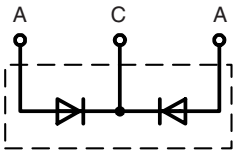
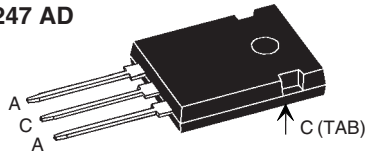
HiPerFRED™ Epitaxial Diode
with common cathode and soft recovery

I_{FAV} = 2x30 A
V_{RRM} = 200 V
t_{rr} = 25 ns

V_{RSM} V	V_{RRM} V	Type
200	200	DSEC 60-02A



TO-247 AD



A = Anode, C = Cathode, TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}		70	A
I_{FAVM}	T_C = 145°C; rectangular, d = 0.5	30	A
I_{FSM}	T_{VJ} = 45°C; t_p = 10 ms (50 Hz), sine	325	A
E_{AS}	T_{VJ} = 25°C; non-repetitive I_{AS} = 3 A; L = 180 µH	1.2	mJ
I_{AR}	$V_A = 1.5 \cdot V_R$ typ.; f = 10 kHz; repetitive	0.3	A
T_{VJ}		-55...+175	°C
T_{VJM}		175	°C
T_{stg}		-55...+150	°C
P_{tot}	T_C = 25°C	165	W
M_d	mounting torque	0.8...1.2	Nm
F_C	mounting force with clip	20...120	N
Weight	typical	6	g

Symbol	Conditions	Characteristic Values typ.	max.	
I_R ①	$V_R = V_{RRM}$; T_{VJ} = 25°C		10	µA
	$V_R = V_{RRM}$; T_{VJ} = 150°C		200	µA
V_F ②	I_F = 30 A; T_{VJ} = 150°C		0.95	V
	T_{VJ} = 25°C		1.20	V
R_{thJC}			0.9	K/W
R_{thCH}		0.25		K/W
t_{rr}	I_F = 1 A; -di/dt = 200 A/µs; V_R = 30 V; T_{VJ} = 25°C	25		ns
I_{RM}	V_R = 100 V; I_F = 50 A; $-di_F/dt$ = 100 A/µs; T_{VJ} = 100°C		4	A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
② Pulse Width = 300 µs, Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified.

Features
- International standard package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM}-values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications
- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{RM} reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

IXYS reserves the right to change limits, test conditions and dimensions.

502

© 2005 IXYS All rights reserved

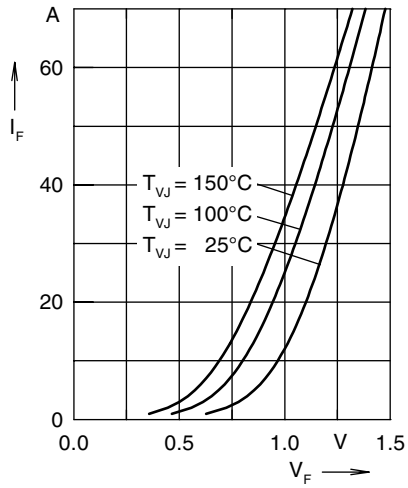


Fig.1 Forward current I_F vs. forward voltage drop V_F

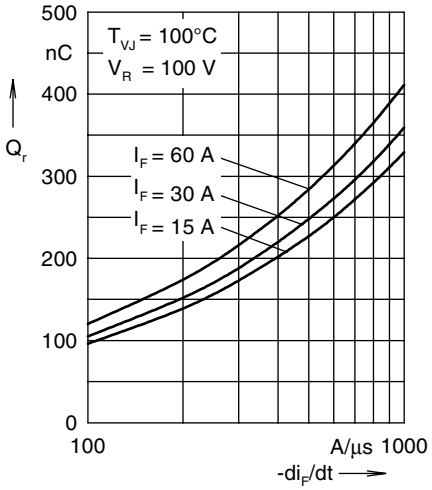


Fig.2 Reverse recovery charge Q_{rr} versus $-di_F/dt$

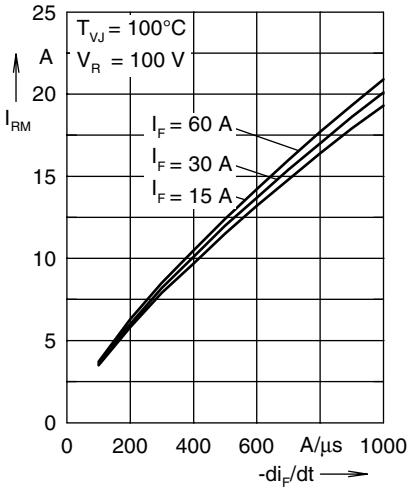


Fig.3 Peak reverse current I_{RM} versus $-di_F/d$

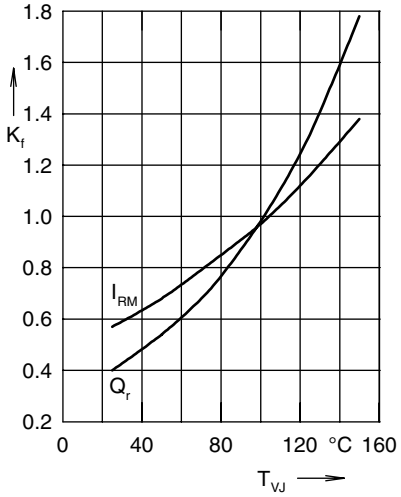


Fig.4 Dynamic parameters Q_{rr}; I_{RM} versus T_{vj}

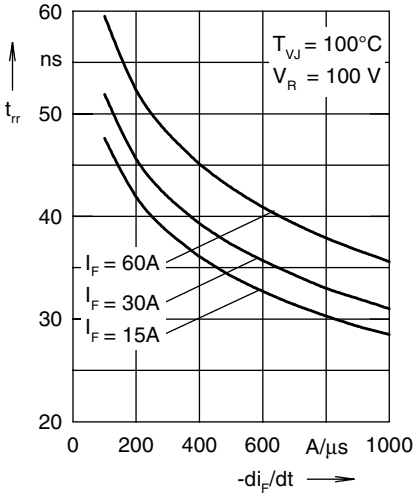


Fig.5 Reverse recovery time t_{rr} versus $-di_F/dt$

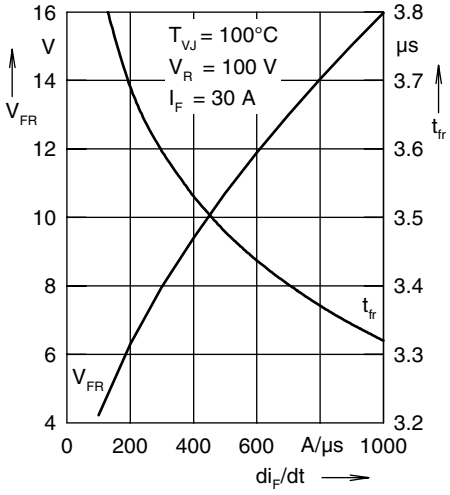


Fig.6 Peak forward voltage V_{FR} & forw. recov. time t_{fr} vs. $-di_F/dt$

NOTE: Fig. 2 to Fig. 6 shows typical values

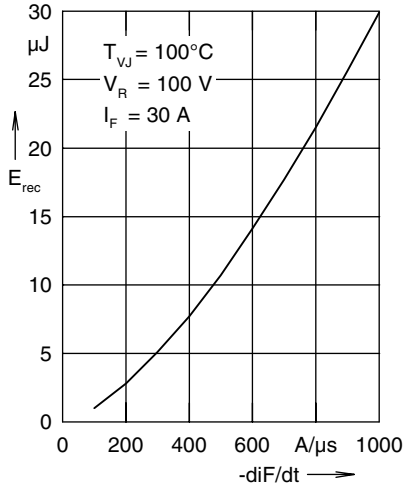


Fig. 7 Recovery energy E_{rec} versus $-di_F/dt$

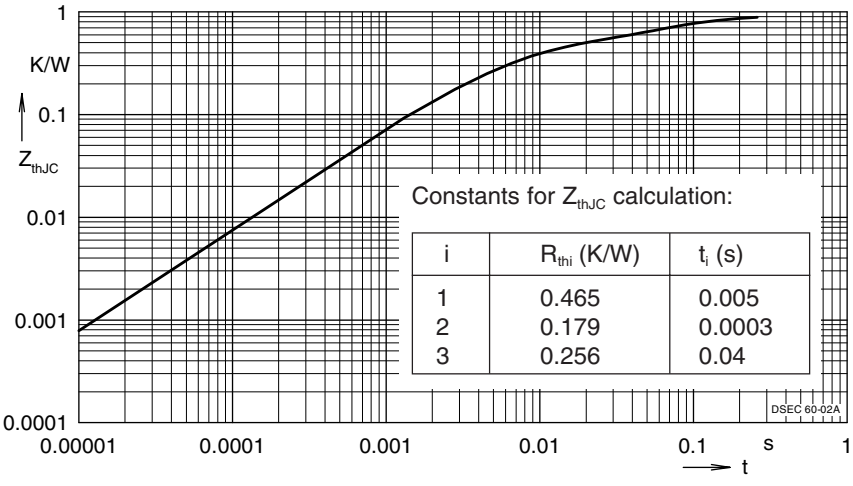


Fig.8 Transient thermal resistance junction to case

IXYS reserves the right to change limits, test conditions and dimensions.

502

© 2005 IXYS All rights reserved